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42V PowerNet

BUK7C10-75AITE

TrenchPLUS standard level FET

Rev. 02 — 18 March 2003 **Product data**

1. Product profile

1.1 Description

N-channel enhancement mode field-effect power transistor in a plastic package using TrenchMOS™ technology, featuring very low on-state resistance. Also includes TrenchPLUS current sensing, and diodes for ESD and temperature protection.

Product availability:

BUK7C10-75AITE in SOT427 (D^2-PAK).

1.2 Features

- Q101 compliant
- ESD protection
- Integrated temperature sensor
- Integrated current sensor.

1.3 Applications

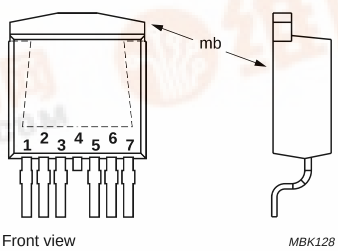
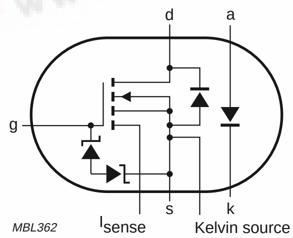
- Variable Valve Timing for engines
- Automotive and power switching
- Electrical Power Assisted Steering
- Fan control.

1.4 Quick reference data

- $V_{DS} \leq 75$ V
- $I_D \leq 114$ A
- $R_{DSon} = 8.8$ mΩ (typ)
- $V_F = 658$ mV (typ)
- $S_F = -1.54$ mV/K (typ)
- $I_D/I_{sense} = 500$ (typ).

2. Pinning information

Table 1: Pinning - SOT427 (D^2-PAK) simplified outline and symbol

Pin	Description	Pin	Description	Simplified outline	Symbol
1	gate (g)	5	cathode (k)		
2	I_{sense}	6	Kelvin source		
3	anode (a)	7	source (s)		
4	drain (d)				
mb	mounting base; connected to drain (d)				

SOT427 (D2-PAK)

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3. Limiting values

Table 2: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage (DC)			-	75	V
V_{DGS}	drain-gate voltage (DC)			-	75	V
V_{GS}	gate-source voltage (DC)			-	±20	V
I_D	drain current (DC)	T_{mb} = 25 °C; V_{GS} = 10 V; Figure 2 and 3	[1]	-	114	A
			[2]	-	75	A
		T_{mb} = 100 °C; V_{GS} = 10 V; Figure 2	[2]	-	75	A
I_{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \leq 10$ µs; Figure 3		-	456	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; Figure 1		-	272	W
$I_{GS(CL)}$	gate-source clamping current	continuous		-	10	mA
		t_p = 5 ms; δ = 0.01		-	50	mA
$V_{isol(FET-TSD)}$	FET to temperature sense diode isolation voltage			-	±100	V
T_{stg}	storage temperature			–55	+175	°C
T_j	junction temperature			–55	+175	°C
Source-drain diode						
I_{DR}	reverse drain current (DC)	T_{mb} = 25 °C	[1]	-	114	A
			[2]	-	75	A
I_{DRM}	peak reverse drain current	T_{mb} = 25 °C; pulsed; $t_p \leq 10$ µs		-	456	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	unclamped inductive load; I_D = 75 A; $V_{DS} \leq 75$ V; V_{GS} = 10 V; R_{GS} = 50 Ω; starting T_j = 25 °C		-	739	mJ
Electrostatic discharge						
V_{esd}	electrostatic discharge voltage; pins 1,2,4,6,7	Human Body Model; C = 100 pF; R = 1.5 kΩ		-	6	kV

[1] Current is limited by power dissipation chip rating

[2] Continuous current is limited by package.

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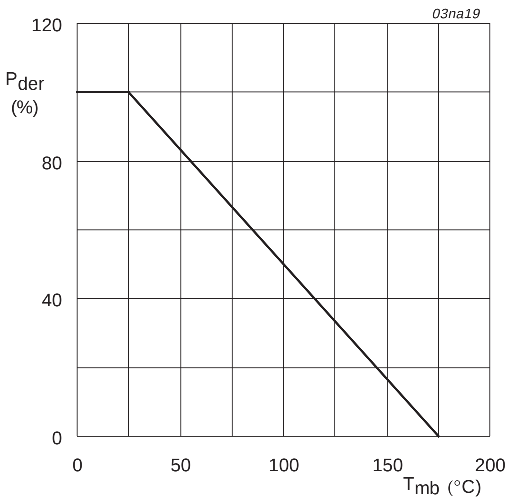
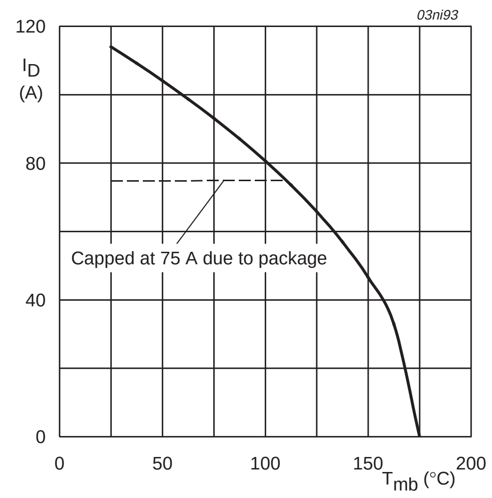


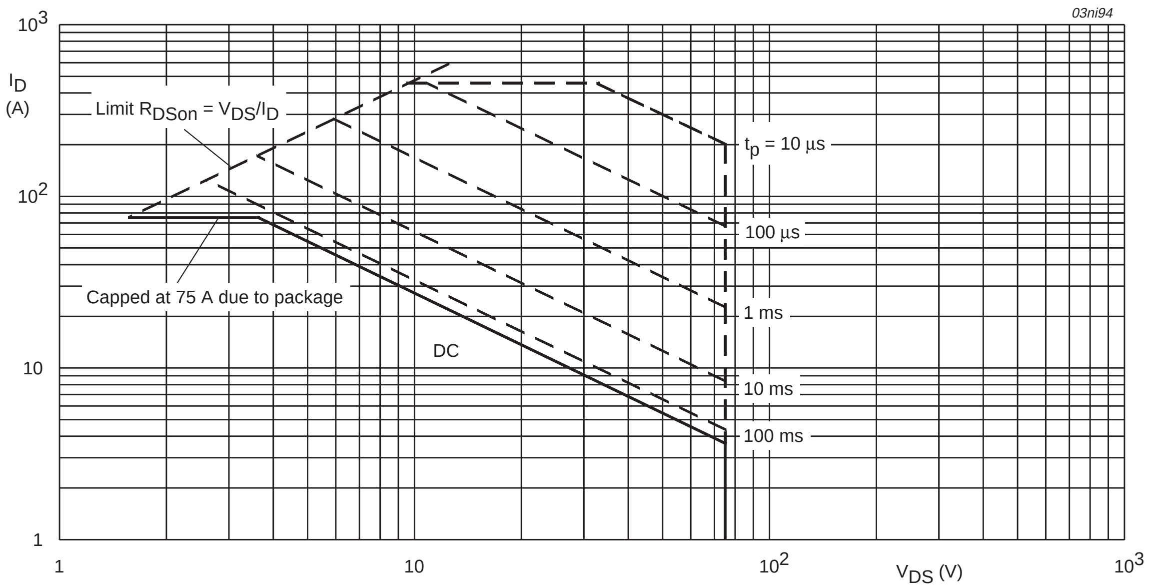
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 1. Normalized total power dissipation as a function of mounting base temperature.



$V_{GS} \geq 10$ V

Fig 2. Continuous drain current as a function of mounting base temperature.



$T_{mb} = 25$ °C; I_{DM} single pulse.

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.

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4. Thermal characteristics

Table 3: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	mounted on printed-circuit board; minimum footprint	-	-	50	K/W
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Figure 4	-	-	0.55	K/W

4.1 Transient thermal impedance

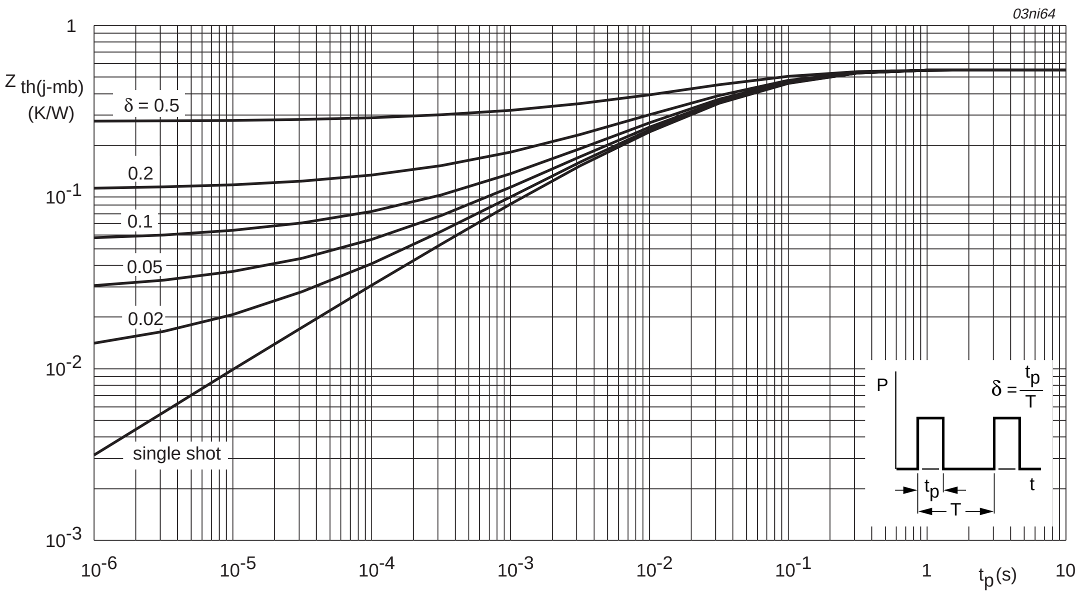

Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration.

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5. Characteristics

Table 4: Characteristics

T_j = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 0.25 mA; V_{GS} = 0 V				
		T_j = 25 °C	75	-	-	V
		T_j = –55 °C	70	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; Figure 9				
		T_j = 25 °C	2	3	4	V
		T_j = 175 °C	1	-	-	V
		T_j = –55 °C	-	-	4.4	V
I_{DSS}	drain-source leakage current	V_{DS} = 75 V; V_{GS} = 0 V				
		T_j = 25 °C	-	0.1	10	µA
		T_j = 175 °C	-	-	250	µA
$V_{(BR)GSS}$	gate-source breakdown voltage	I_G = ±1 mA; –55 °C < T_j < 175 °C	20	22	-	V
I_{GSS}	gate-source leakage current	V_{GS} = ±10 V; V_{DS} = 0 V				
		T_j = 25 °C	-	22	1000	nA
		T_j = 175 °C	-	-	10	µA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 50 A; Figure 7 and 8				
		T_j = 25 °C	-	8.8	10	mΩ
		T_j = 175 °C	-	-	21	mΩ
V_F	forward voltage, temperature sense diode	I_F = 250 µA	648	658	668	mV
S_F	temperature coefficient temperature sense diode	I_F = 250 µA; –55 °C < T_j < 175 °C	–1.4	–1.54	–1.68	mV/K
V_{hys}	forward voltage hysteresis temperature sense diode	125 µA < I_F < 250 µA	25	32	50	mV
I_D/I_{sense}	ratio of drain current to sense current	V_{GS} > 10 V; –55 °C < T_j < 175 °C	450	500	550	
Dynamic characteristics						
$Q_{g(tot)}$	total gate charge	V_{GS} = 10 V; V_{DS} = 60 V; I_D = 25 A; Figure 14	-	121	-	nC
Q_{gs}	gate-source charge		-	20	-	nC
Q_{gd}	gate-drain (Miller) charge		-	44	-	nC
C_{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz; Figure 12	-	4700	-	pF
C_{oss}	output capacitance		-	800	-	pF
C_{rss}	reverse transfer capacitance		-	455	-	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 30 V; R_L = 1.2 Ω; V_{GS} = 10 V; R_G = 10 Ω	-	35	-	nS
t_r	rise time		-	108	-	nS
$t_{d(off)}$	turn-off delay time		-	185	-	nS
t_f	fall time		-	100	-	nS

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Table 4: Characteristics...*continued*

T_j = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
L_d	internal drain inductance	measured from upper edge of drain mounting base to centre of die	-	2.5	-	nH
L_s	internal source inductance	measured from source lead to source bond pad	-	7.5	-	nH
Source-drain diode						
V_{SD}	source-drain (diode forward) voltage	I_S = 25 A; V_{GS} = 0 V; Figure 18	-	0.85	1.2	V
t_{rr}	reverse recovery time	I_S = 20 A; dI_S/dt = –100 A/µs V_{GS} = –10 V; V_{DS} = 30 V	-	75	-	ns
Q_r	recovered charge		-	270	-	nC

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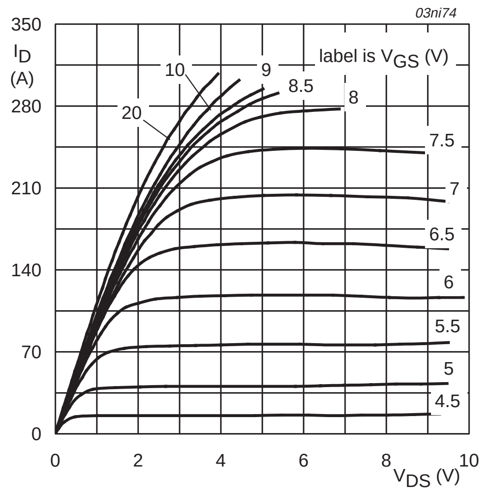
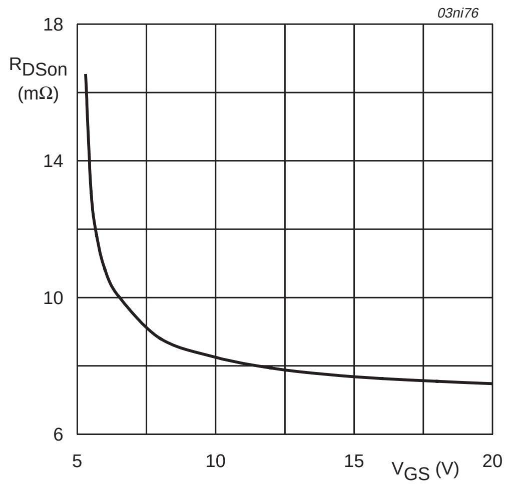


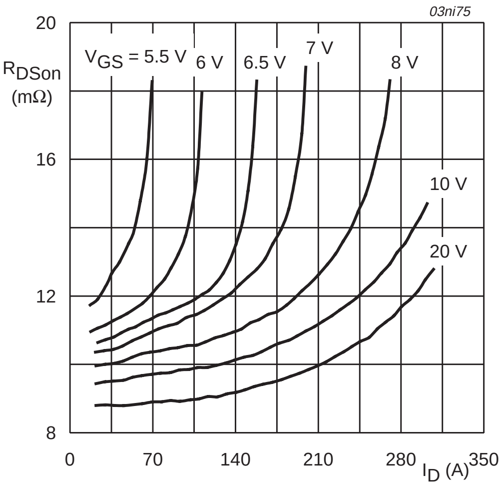
T_j = 25 °C; t_p = 300 μs

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values.



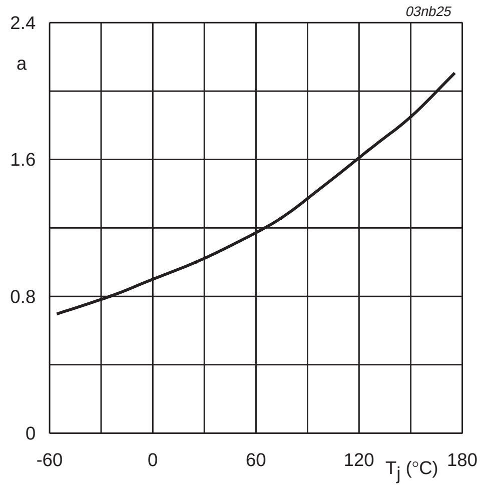
T_j = 25 °C; I_D = 50 A

Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values.



T_j = 25 °C; t_p = 300 μs

Fig 7. Drain-source on-state resistance as a function of drain current; typical values.



$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$

Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature.

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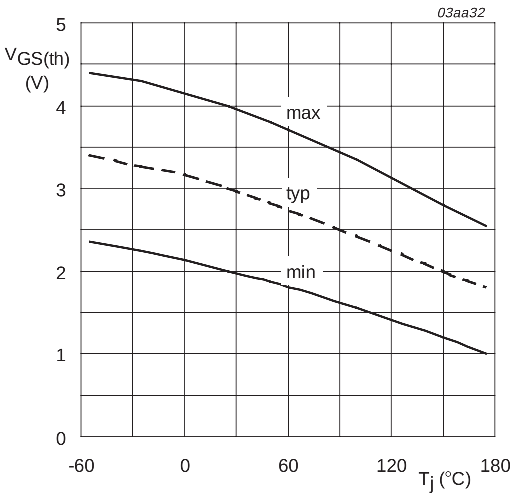
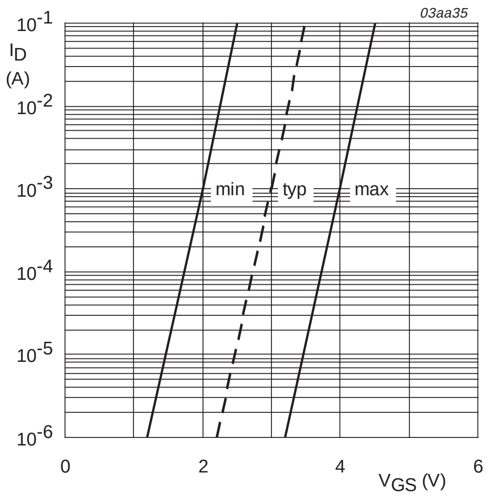


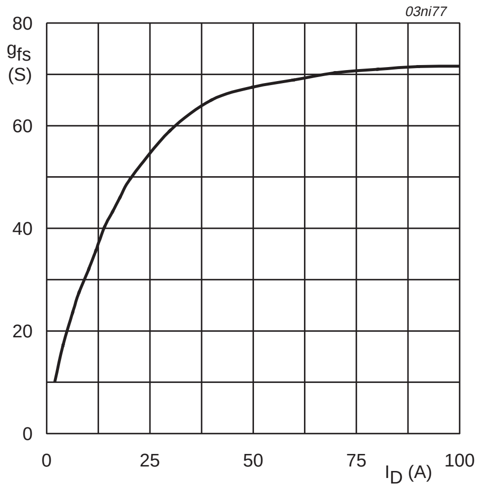
I_D = 1 mA; $V_{DS} = V_{GS}$

Fig 9. Gate-source threshold voltage as a function of junction temperature.



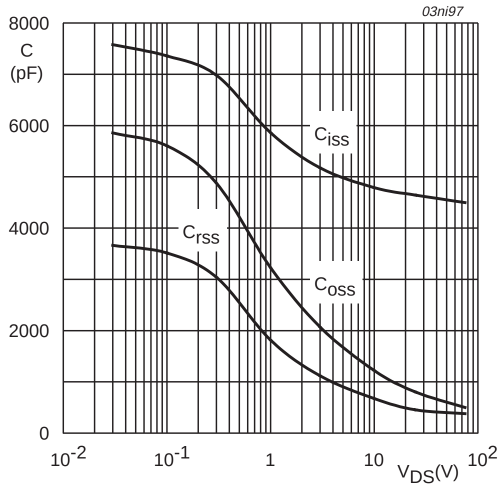
T_j = 25 °C; $V_{DS} = V_{GS}$

Fig 10. Sub-threshold drain current as a function of gate-source voltage.



T_j = 25 °C; V_{DS} = 25 V

Fig 11. Forward transconductance as a function of drain current; typical values.



V_{GS} = 0 V; f = 1 MHz

Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.

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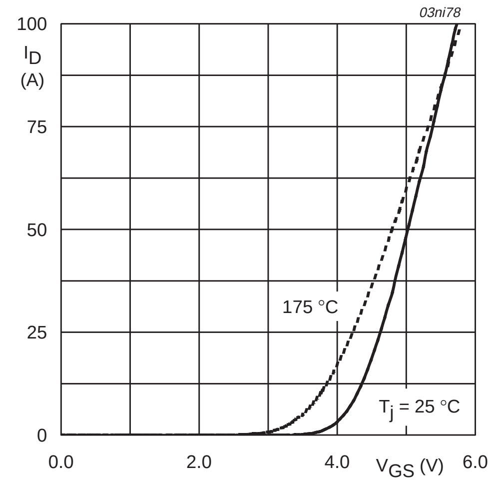
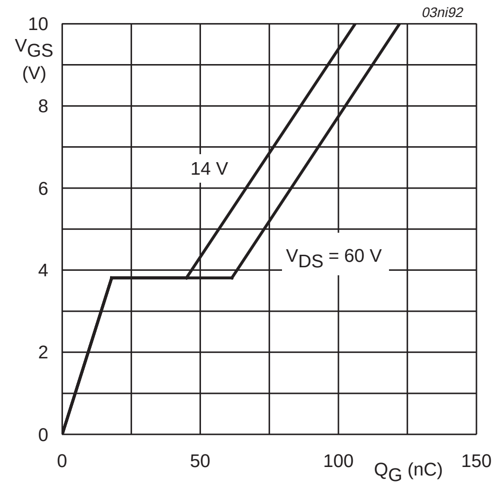


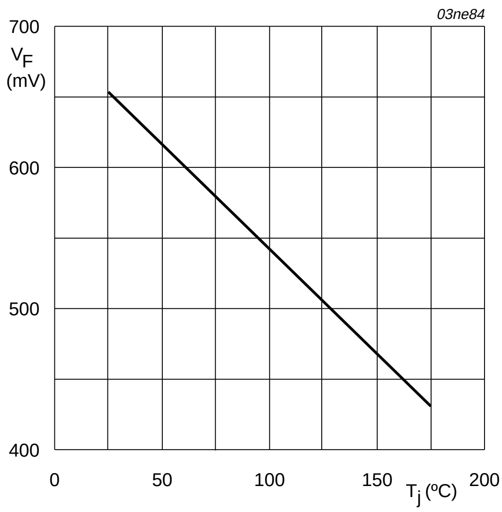
V_{DS} = 25 V

Fig 13. Transfer characteristics: drain current as a function of gate-source voltage; typical values.



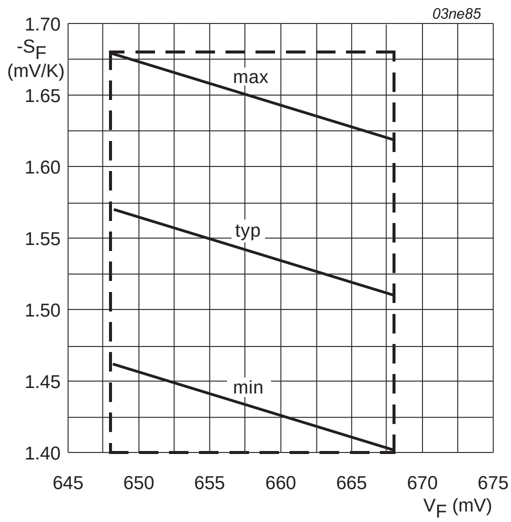
T_j = 25 °C; I_D = 25 A

Fig 14. Gate-source voltage as a function of turn-on gate charge; typical values.



I_F = 250 µA

Fig 15. Forward voltage of temperature sense diode as a function of junction temperature; typical values.



V_F at T_j = 25 °C; I_F = 250 µA

Fig 16. Temperature coefficient of temperature sense diode as a function of forward voltage; typical values.

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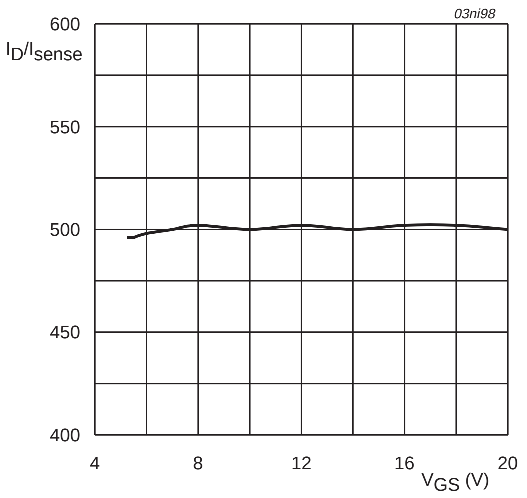
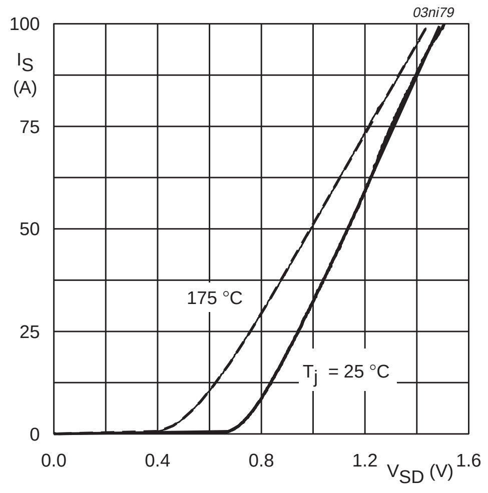


I_D = 25 A

Fig 17. Drain-sense current ratio as a function of gate-source voltage; typical values.



V_{GS} = 0 V

Fig 18. Reverse diode current as function of reverse diode voltage; typical values.

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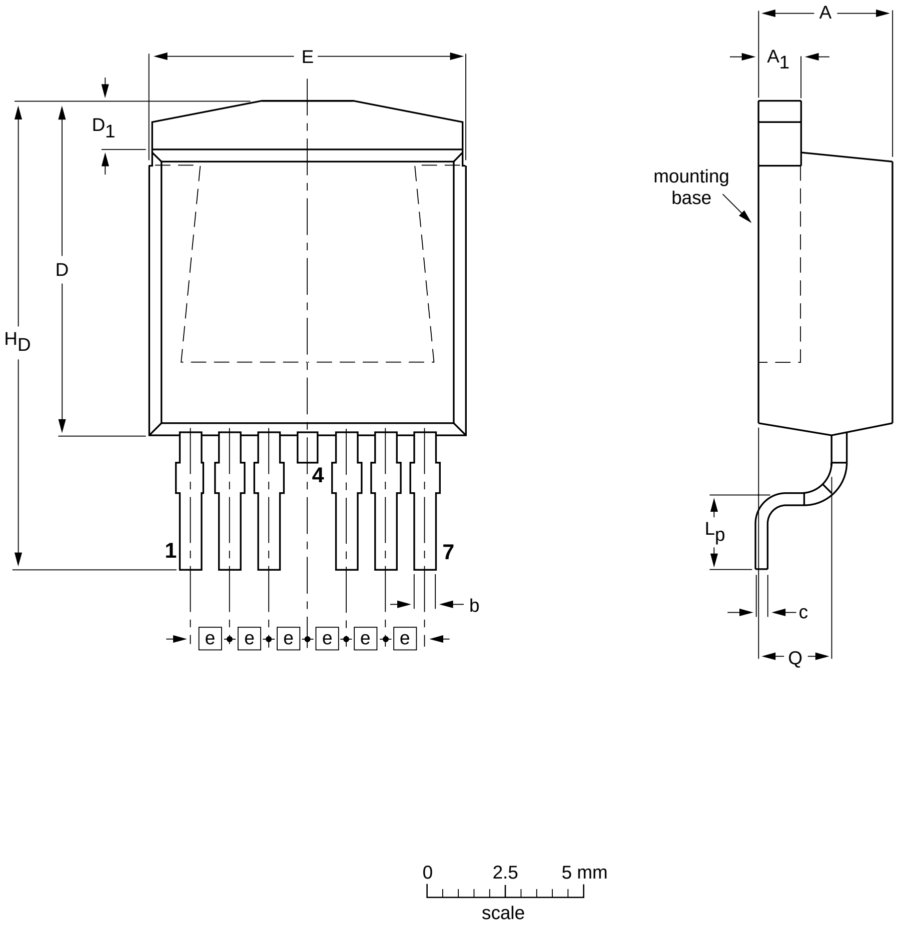
6. Package outline

Plastic single-ended surface mounted package (Philips version of D2-PAK); 7 leads (one lead cropped) **SOT427**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	c	D max.	D_1	E	e	L_p	H_D	Q
mm	4.50 4.10	1.40 1.27	0.85 0.60	0.64 0.46	11	1.60 1.20	10.30 9.70	1.27	2.90 2.10	15.80 14.80	2.60 2.20

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT427						~~99-06-25~~ 01-04-18

Fig 19. SOT427 (D^2-PAK).

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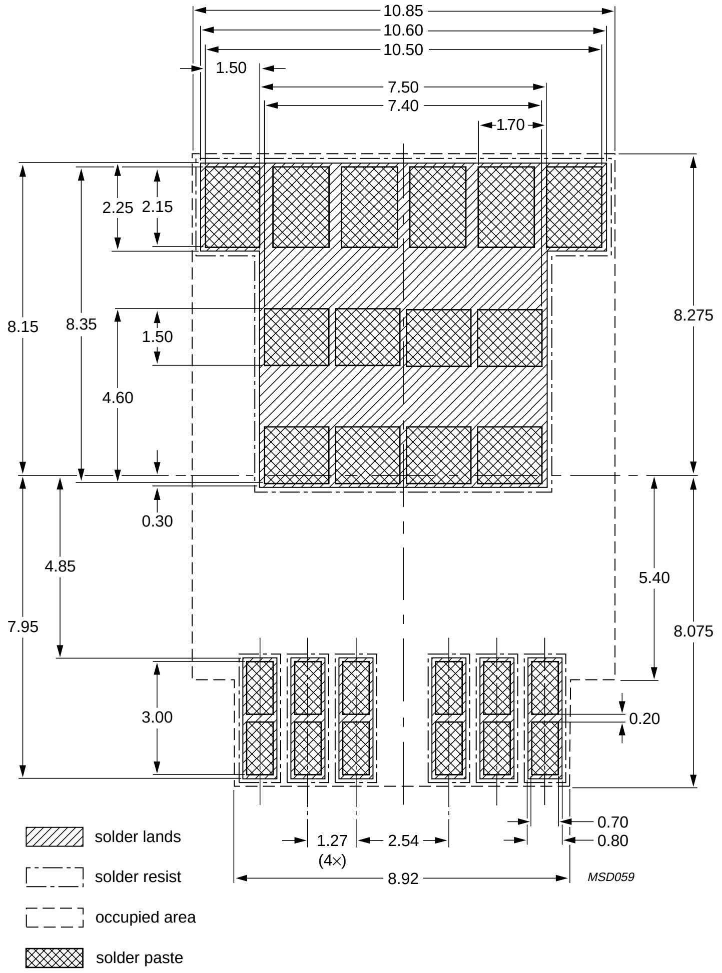
7. Soldering



Dimensions in mm.

Fig 20. Reflow soldering footprint for SOT427.

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8. Revision history

Table 5: Revision history

Rev	Date	CPCN	Description
02	20030318	-	**Product data (9397 750 11048)** Modification: • Correction to Figure 3
01	20020725	-	**Product data (9397 750 09881)**

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9. Data sheet status

Level	Data sheet status[1]	Product status[2][3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

[1] Please consult the most recently issued data sheet before initiating or completing a design.

[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

10. Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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